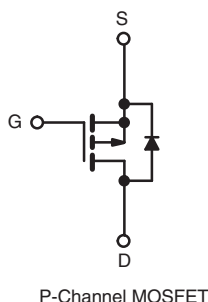
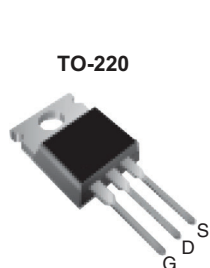


Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	- 200	
$R_{DS(on)}$ (Ω)	$V_{GS} = -10\text{ V}$	3.0
Q_g (Max.) (nC)	11	
Q_{gs} (nC)	7.0	
Q_{gd} (nC)	4.0	
Configuration	Single	



FEATURES

- Dynamic dV/dt Rating
- P-Channel
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead (Pb)-free Available



RoHS*
COMPLIANT

DESCRIPTION

The Power MOSFETs technology is the key to Vishay's advanced line of Power MOSFET transistors. The efficient geometry and unique processing of the Power MOSFETs design achieve very low on-state resistance combined with high transconductance and extreme device ruggedness.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.

ORDERING INFORMATION

Package	TO-220
Lead (Pb)-free	IRF9610PbF SiHF9610-E3
SnPb	IRF9610 SiHF9610

ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	- 200	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	$V_{GS} \text{ at } -10\text{ V}$	$T_C = 25$	A
		$T_C = 100$	
Pulsed Drain Current ^a	I_{DM}	- 7.0	
Linear Derating Factor		0.16	W/ $^{\circ}\text{C}$
Maximum Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	20
Inductive Current, Clamp	I_{LM}	- 7.0	A
Peak Diode Recovery dV/dt^c	dV/dt	- 5.0	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^{\circ}\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d	
Mounting Torque	6-32 or M3 screw	10	
		1.1	N · m

Notes



- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 5).
- Not applicable.
- $I_{SD} \leq -1.8\text{ A}$, $dI/dt \leq 70\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^{\circ}\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

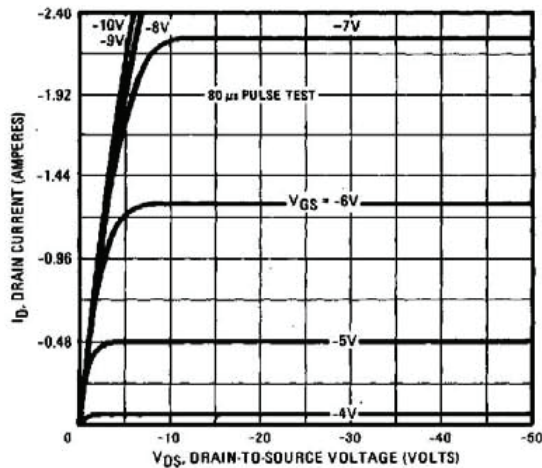
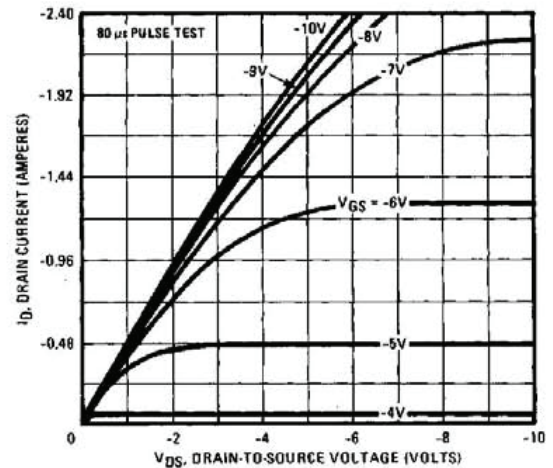
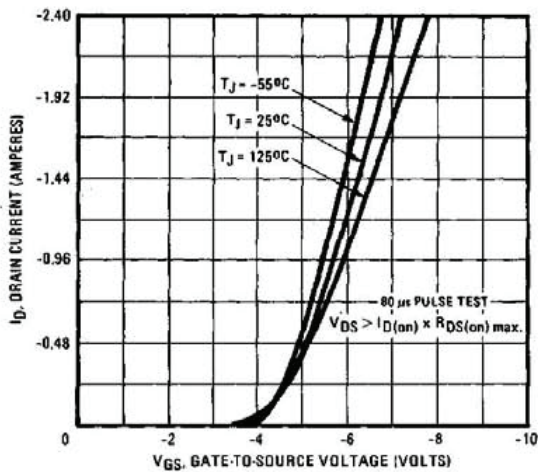
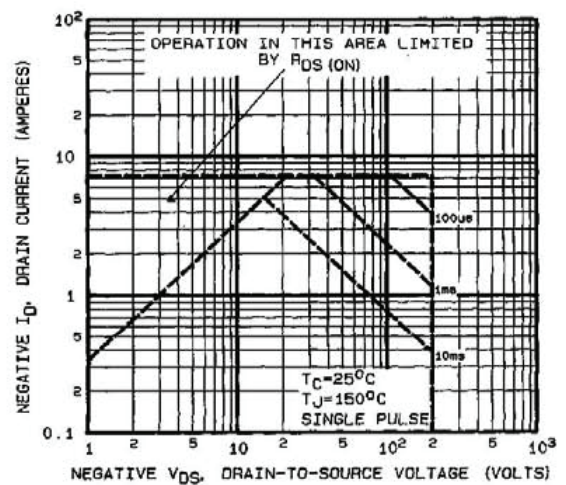
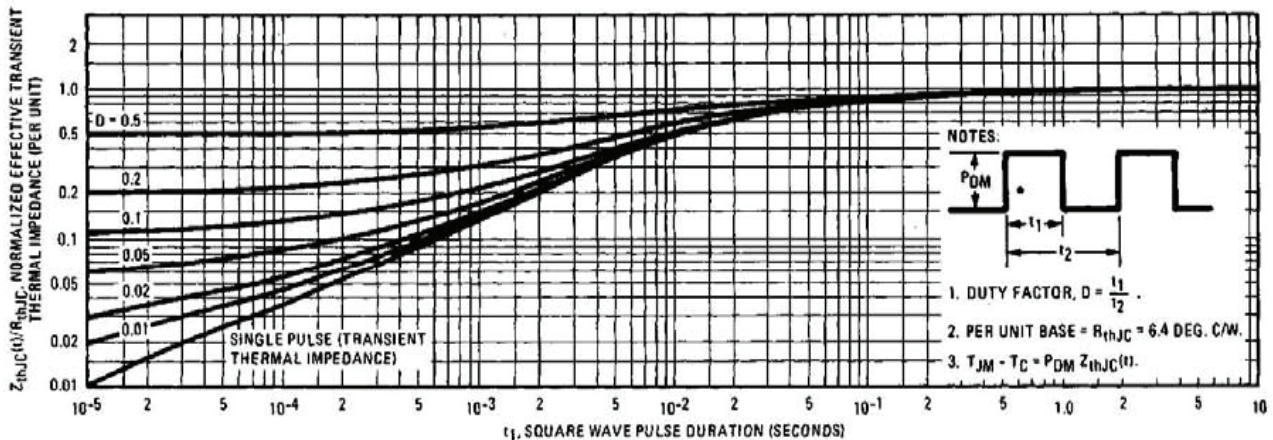
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	6.4	

SPECIFICATIONS $T_J = 25\text{ °C}$, unless otherwise noted

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA		- 200	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = - 1 mA		-	- 0.23	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA		- 2.0	-	- 4.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 200 V, V _{GS} = 0 V		-	-	- 100	μA
		V _{DS} = - 160 V, V _{GS} = 0 V, T _J = 125 °C		-	-	- 500	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = - 10 V	I _D = -0.90 A ^b	-	-	3.0	Ω
Forward Transconductance	g _{fs}	V _{DS} = - 50 V, I _D = - 0.90 A ^b		0.90	-	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = - 25 V, f = 1.0 MHz, see fig. 10		-	170	-	pF
Output Capacitance	C _{oss}			-	50	-	
Reverse Transfer Capacitance	C _{rss}			-	15	-	
Total Gate Charge	Q _g	V _{GS} = - 10 V	I _D = - 3.5 A, V _{DS} = - 160 V, see fig. 11 and 18 ^b	-	-	11	nC
Gate-Source Charge	Q _{gs}			-	-	7.0	
Gate-Drain Charge	Q _{gd}			-	-	4.0	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 100 V, I _D = - 0.90 A, R _G = 50 Ω, R _D = 11 Ω, see fig. 17 ^b		-	8.0	-	ns
Rise Time	t _r			-	15	-	
Turn-Off Delay Time	t _{d(off)}			-	10	-	
Fall Time	t _f			-	8.0	-	
Internal Drain Inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal Source Inductance	L _S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	- 1.8	A
Pulsed Diode Forward Current ^a	I _{SM}			-	-	- 7.0	
Body Diode Voltage	V _{SD}	T _J = 25 °C, I _S = - 1.8 A, V _{GS} = 0 V ^b		-	-	- 5.8	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = - 1.8 A, dI/dt = 100 A/μs ^b		-	240	360	ns
Body Diode Reverse Recovery Charge	Q _{rr}			-	1.7	2.6	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 5).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Fig. 1 - Typical Output Characteristics

Fig. 3 - Typical Saturation Characteristics

Fig. 2 - Typical Transfer Characteristics

Fig. 4 - Maximum Safe Operating Area

Fig. 5 - Maximum Effective Transient Thermal Impedance, Junction-to-Case vs. Pulse Duration

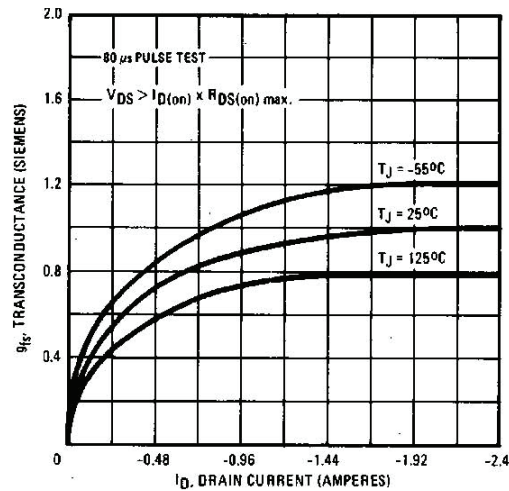


Fig. 6 - Typical Transconductance vs. Drain Current

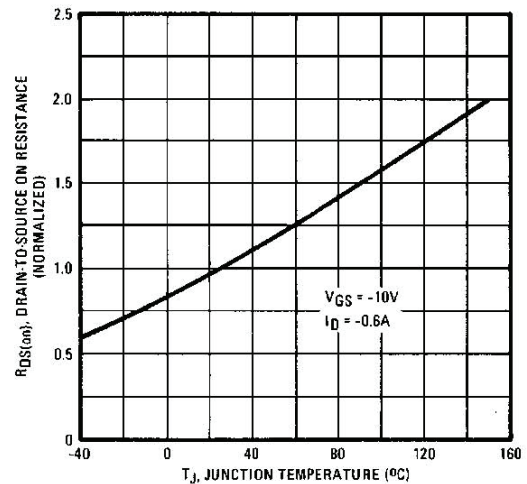


Fig. 9 - Normalized On-Resistance vs. Temperature

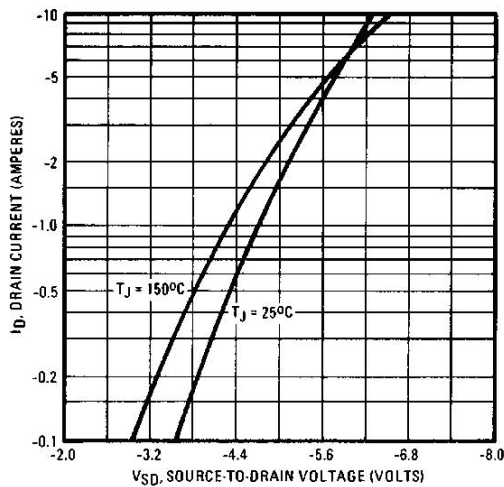


Fig. 7 - Typical Source-Drain Diode Forward Voltage

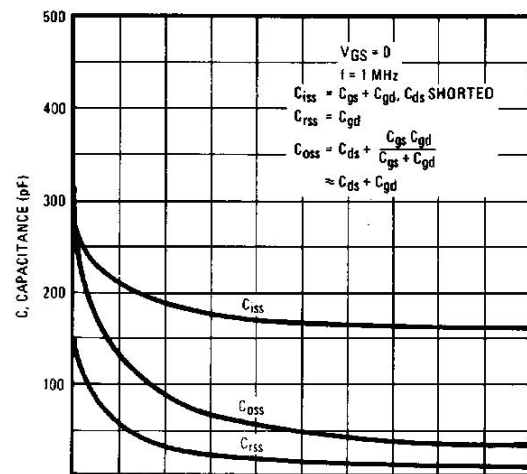


Fig. 10 - Typical Capacitance vs. Drain-to-Source Voltage

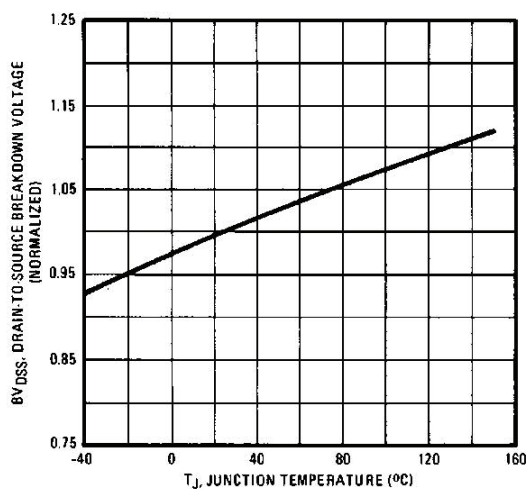


Fig. 8 - Breakdown Voltage vs. Temperature

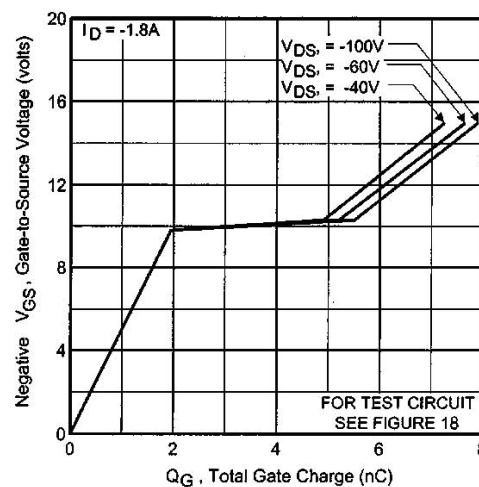
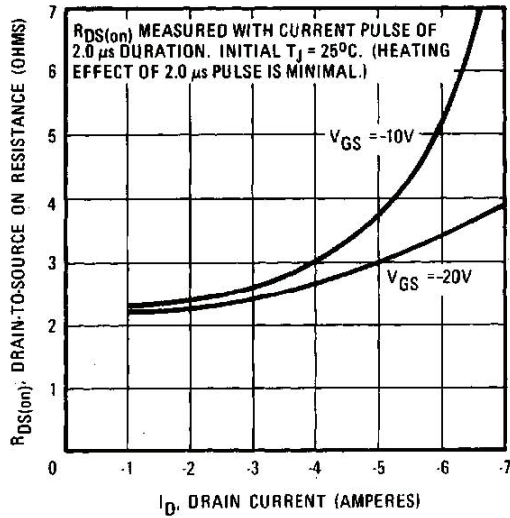
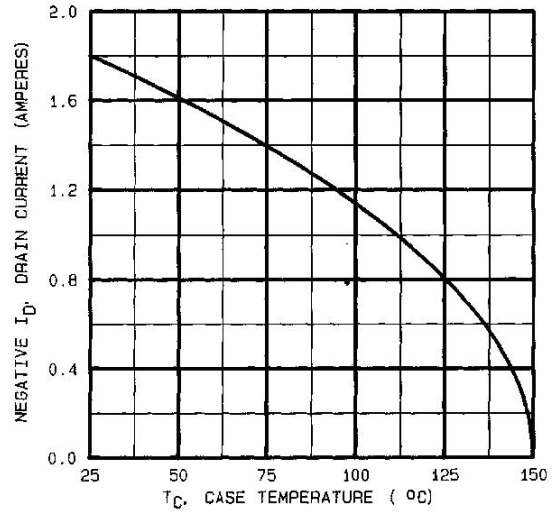
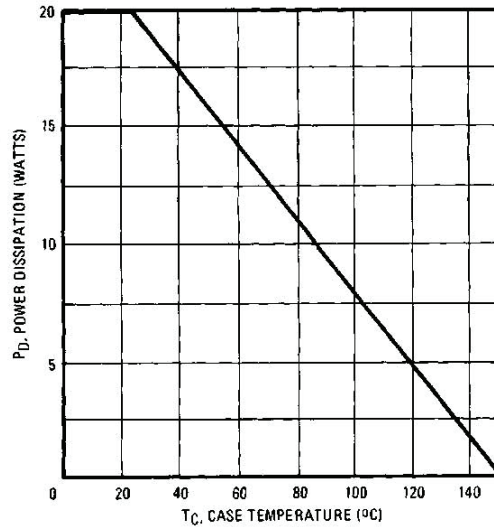
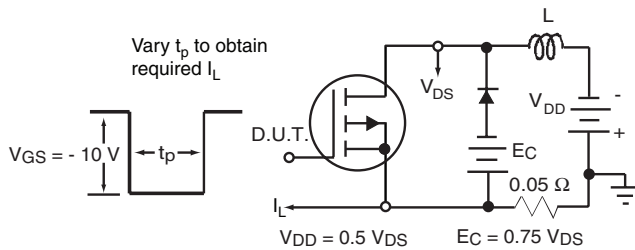
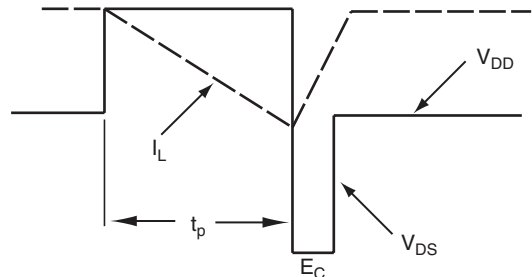


Fig. 11 - Typical Gate Charge vs. Gate-to-Source Voltage


Fig. 12 - Typical On-Resistance vs. Drain Current

Fig. 13 - Maximum Drain Current vs. Case Temperature

Fig. 14 - Power vs. Temperature Derating Curve

Fig. 15 - Clamped Inductive Test Circuit

Fig. 16 - Clamped Inductive Waveforms

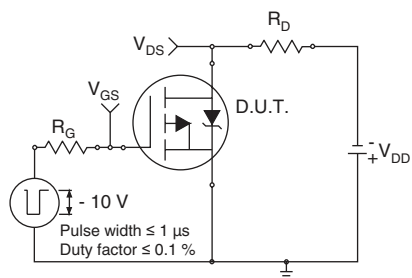


Fig. 17a - Switching Time Test Circuit

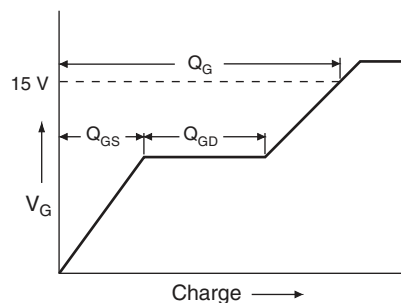


Fig. 18a - Basic Gate Charge Waveform

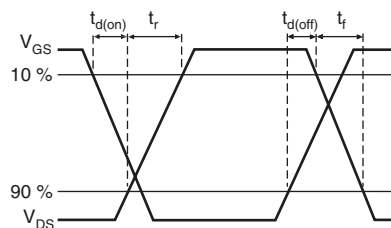


Fig. 17b - Switching Time Waveforms

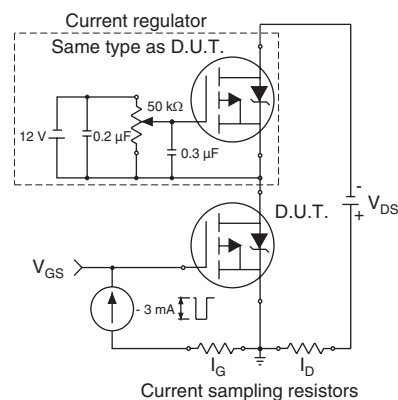
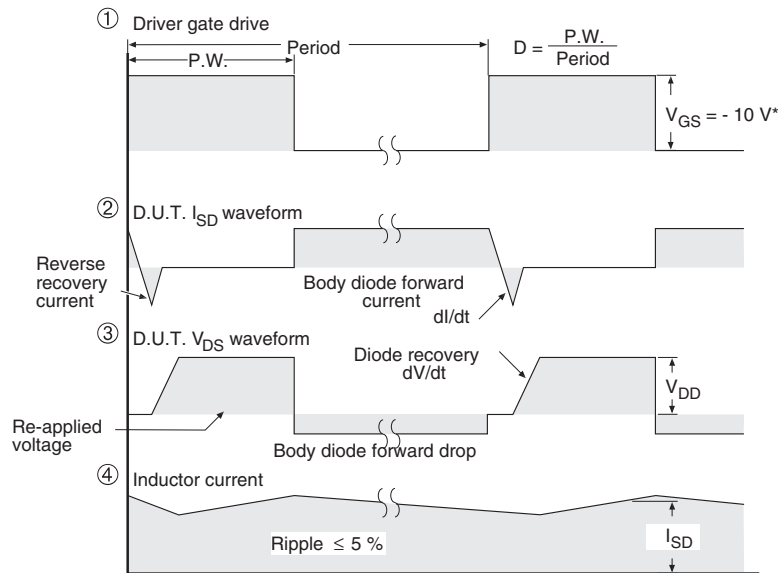
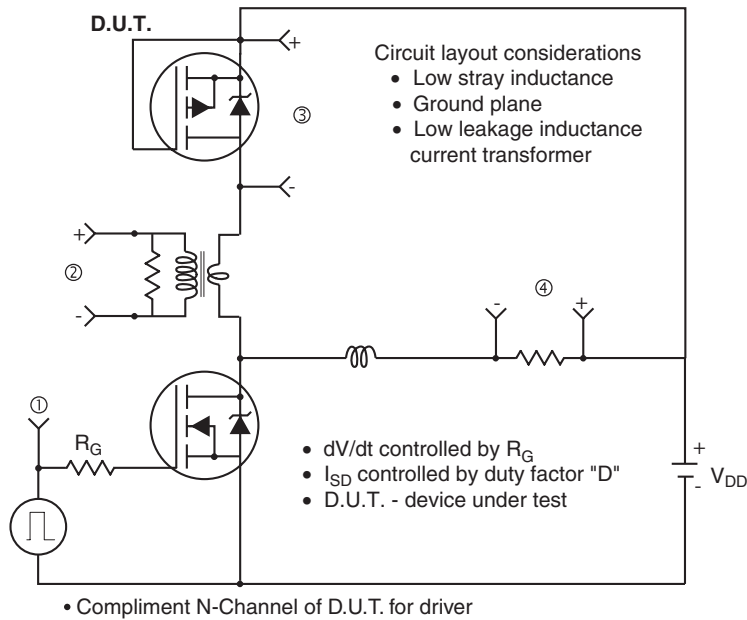


Fig. 18b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = -5\text{ V}$ for logic level and -3 V drive devices

Fig. 19 - For P-Channel

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